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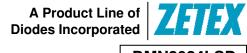












DMN3024LSD

30V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
30V	24mΩ @ V _{GS} = 10V	7.2A
30 V	36mΩ @ V _{GS} = 4.5V	5.8A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- DC-DC Converters
- · Power management functions

Features and Benefits

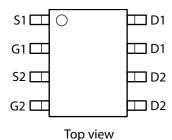
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

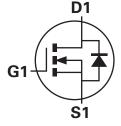
Mechanical Data

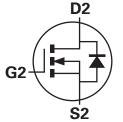
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)











Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
DMN3024LSD-13	N3024LD	13	12	2,500	

Note:

Marking Information



N3024LD = Product Type Marking Code

Oli = Manufacturer's Marking

YYWW = Date Code Marking

YY = Year (ex: 09 = 2009)

WW = Week (01-52)

^{1.} Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.





Maximum Ratings @TA = 25°C unless otherwise specified

Ch	naracteristic		Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	30	V
Gate-Source voltage			V_{GS}	±20	V
Continuous Drain current		(Notes 3 & 5)	I _D	7.2	
	V _{GS} = 10V	T _A = 70°C (Notes 3 & 5)		5.8	^
		(Notes 2 & 5)		5.7	А
		(Notes 2 & 6)		6.8	
Pulsed Drain current V _{GS} = 10V		(Notes 4 & 5)	I _{DM}	34	Α
Continuous Source current (Body diode) (Notes 3 & 5		(Notes 3 & 5)	I _S	3.3	Α
Pulsed Source current (Body diode) (Notes 4 & 5)		I _{SM}	34	Α	

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Notes 2 & 5)		1.3 10.0		
Power dissipation Linear derating factor	(Notes 2 & 6)	P_{D}	1.8 14.3	W mW/°C	
	(Notes 3 & 5)		2.0 15.9		
Thermal Resistance, Junction to Ambient	(Notes 2 & 5) (Notes 2 & 6)	$R_{ hetaJA}$	100 70	°C/W	
Thermal Resistance, Junction to Lead	(Notes 3 & 5) (Notes 5 & 7)	R _e JL	63 53	°C/W	
Operating and storage temperature range	Ì	T _J , T _{STG}	-55 to 150	°C	

- 2. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is 2. For a device strate mounted of 25mm x 25mm x 1.5mm Fn4 FoB with high coverage of single sided 102 copper, in still all conditions, the device is measured when operating in a steady-state condition.

 3. Same as note (2), except the device is measured at t ≤ 10 sec.

 4. Same as note (2), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.

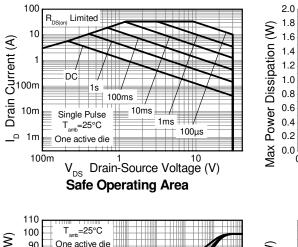
 5. For a device with one active die.

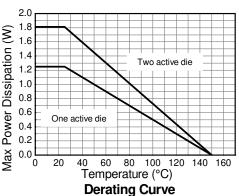
 6. For a device with two active die running at equal power.

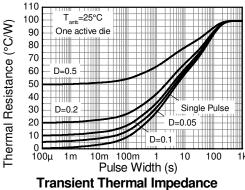
- 7. Thermal resistance from junction to solder-point (at the end of the drain lead): the device is operating in a steady-state condition.

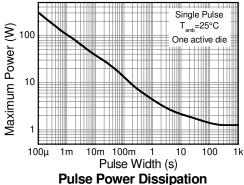


Thermal Characteristics













Electrical Characteristics @TA = 25°C unless otherwise specified

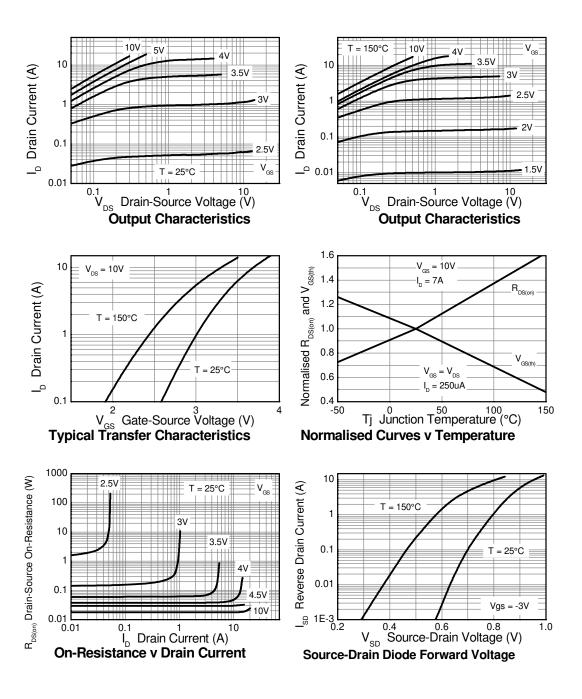
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μА	V _{DS} = 30V, V _{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V		
ON CHARACTERISTICS	ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0		3.0	V	$I_D=250\mu A,\ V_{DS}=V_{GS}$		
Static Drain-Source On-Resistance (Note 8)	D		_	0.024	Ω	V _{GS} = 10V, I _D = 7.0A		
Static Diam-Source On-Nesistance (Note 6)	R _{DS (ON)}			0.036	22	V _{GS} = 4.5V, I _D = 6.0A		
Forward Transconductance (Notes 8 & 9)	g fs	_	16.5	_	S	V _{DS} = 15V, I _D = 7.1A		
Diode Forward Voltage (Note 8)	V_{SD}	_	0.82	1.2	V	I _S = 1.7A, V _{GS} = 0V		
Reverse recovery time (Note 9)	t _{rr}		12	_	ns	1 0 0 0 1:/14 100 0 / 5		
Reverse recovery charge (Note 9)	Q _{rr}	_	4.8	_	nC	I _S = 2.2A, di/dt= 100A/μs		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}	_	608	_	pF			
Output Capacitance	Coss	_	132		pF	V _{DS} = 15V, V _{GS} = 0V -f= 1MHz		
Reverse Transfer Capacitance	C _{rss}	_	71		pF	- I = 1 IVI 12		
Total Gate Charge	Qg	_	6.3	_	nC	V _{DS} = 15V, V _{GS} = 4.5V I _D = 7A		
Total Gate Charge	Qg	_	12.9	_	nC			
Gate-Source Charge	Q _{gs}	_	2.5	_	nC	$V_{DS} = 15V, V_{GS} = 10V$		
Gate-Drain Charge	Q_{gd}	_	2.5	_	nC	-I _D = 7A		
Turn-On Delay Time (Note 10)	t _{D(on)}	_	2.9	_	ns			
Turn-On Rise Time (Note 10)	t _r	_	3.3		ns	V _{DD} = 15V, V _{GS} = 10V		
Turn-Off Delay Time (Note 10)	t _{D(off)}	_	16		ns	$I_D=$ 1A, $R_G\cong 6.0\Omega$		
Turn-Off Fall Time (Note 10)	t _f	_	8		ns			

Notes:

- 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%$
- For design aid only, not subject to production testing.
 Switching characteristics are independent of operating junction temperatures.

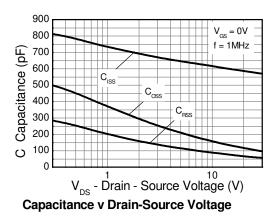


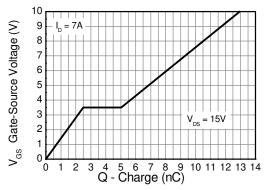
Typical Characteristics





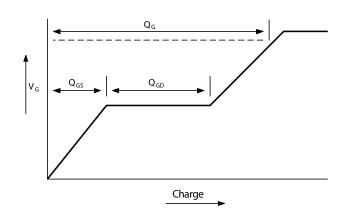
Typical Characteristics - continued





Gate-Source Voltage v Gate Charge

Test Circuits



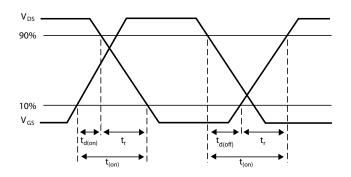
Current regulator

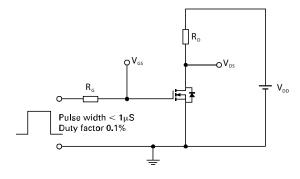
12V 0.2µF 50k D.U.T

Vos

Basic gate charge waveform

Gate charge test circuit



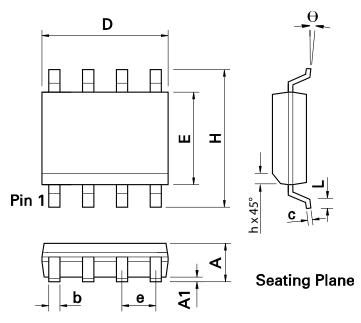


Switching time waveforms

Switching time test circuit

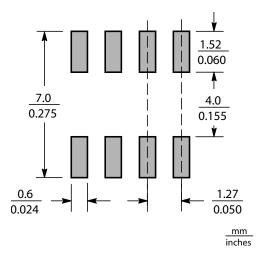


Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	0.053	0.069	1.35	1.75	е	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	С	0.008	0.010	0.19	0.25
Н	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
Е	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Suggested Pad Layout







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